

Automotive Power



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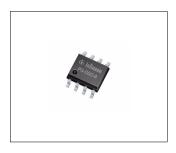


LIN Transceiver TLE6258-2G



Features

- Single-wire transceiver, suitable for LIN protocol
- Compatible to LIN specification 1.2, 1.3 and 2.0
- Compatible to ISO 9141 functions
- Transmission rate up to 20 kBaud
- Very low current consumption in stand-by mode
- Wake-up from Bus
- Short circuit proof to ground and battery
- Overtemperature protection
- Green Product (RoHS compliant)
- AEC Qualified



Description

The single wire transceiver TLE6258-2G is a monolithic integrated circuit in a PG-DSO-8 package. It works as an interface between the protocol controller and the physical bus. The TLE6258-2G is especially suitable to drive the bus line in LIN systems in automotive and industrial applications. Further it can be used in standard ISO9141 systems.

In order to reduce the current consumption the TLE6258-2G offers a stand-by mode. A wake-up caused by a message on the bus sets the RxD output low until the device is switched to normal operation mode.

The IC is based on the Smart Power Technology SPT® which allows bipolar and CMOS control circuitry in accordance with DMOS power devices existing on the same monolithic circuit.

The TLE6258-2G is designed to withstand the severe conditions of automotive applications.

Туре	Package
TLE6258-2G	PG-DSO-8



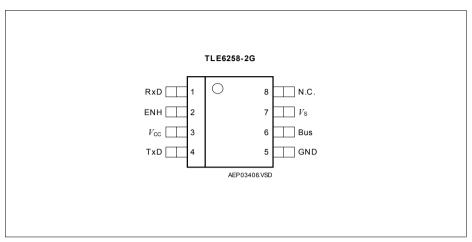


Figure 1 Pin Configuration (top view)

Table 1 Pin Definitions and Functions

Pin No.	Symbol	Function
1	RxD	Receive data output; integrated pull-up, LOW in dominant state
2	ENN	Enable not input; integrated 30 k Ω pull-up, transceiver in normal operation mode when LOW
3	$V_{\sf CC}$	5 V supply input
4	TxD	Transmit data input; integrated pull-up, LOW in dominant state
5	GND	Ground
6	Bus	Bus output/input; internal 30 $k\Omega$ pull-up, LOW in dominant state
7	V_{S}	Battery supply input
8	n.c.	Not connected

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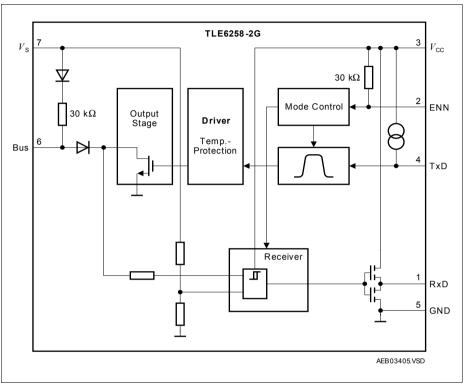


Figure 2 Functional Block Diagram

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Application Information

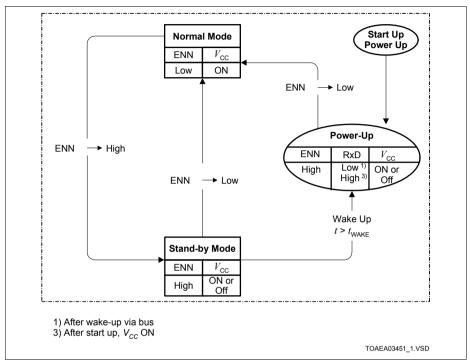


Figure 3 State Diagram

For fail safe reasons the TLE6258-2G has already a pull-up resistor of 30 k Ω implemented. To achieve the required timings for the dominant to recessive transition of the bus signal an additional external termination resistor of 1 k Ω is required. It is recommended to place this resistor in the master node. To avoid reverse currents from the bus line into the battery supply line in case of an unpowered node, it is recommended to place a diode in series to the external pull-up. For small systems (low bus capacitance) the EMC performance of the system is supported by an additional capacitor of at least 1 nF in the master node (see **Figure 6**).

In order to reduce the current consumption the TLE6258-2G offers a stand-by mode. This mode is selected by switching the Enable Not (ENN) input high (see **Figure 3**). In the stand-by mode a wake-up caused by a message on the bus is indicated by setting the RxD output low. When entering the normal mode this wake-up flag is reset and the RxD output is released to transmit the bus data.

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Table 2 Absolute Maximum Ratings

Parameter	Symbol	Limit	Values	Unit	Remarks
		Min.	Max.		
Voltages					
Supply voltage	$V_{\sf CC}$	-0.3	6	٧	_
Battery supply voltage	V_{S}	-0.3	40	٧	-
Bus input voltage	V_{bus}	-20	32	٧	-
Bus input voltage	V_{bus}	-20	40	٧	t < 1 s
Logic voltages at EN, TxD, RxD	V_{I}	-0.3	V _{CC} + 0.3	V	$0 \text{ V} < V_{\text{CC}} < 5.5 \text{ V}$
Electrostatic discharge voltage at $V_{\rm S}$, Bus	V_{ESD}	-4	4	kV	human body model (100 pF via 1.5 k Ω)
Electrostatic discharge voltage	V_{ESD}	-2	2	kV	human body model (100 pF via 1.5 k Ω)
Temperatures	·			•	
Junction temperature	$T_{\rm j}$	-40	150	°C	_

Note: Maximum ratings are absolute ratings; exceeding any one of these values may cause irreversible damage to the integrated circuit

Table 3 Operating Range

Parameter	er Symbol Limit Values		Unit	Remarks			
		Min.	Max.				
Supply voltage	$V_{\sf CC}$	4.5	5.5	٧	_		
Battery Supply Voltage	V_{S}	6	35	٧	_		
Junction temperature	$T_{\rm j}$	-40	150	°C	_		
Thermal Shutdown (junction	temperat	ure)					
Thermal shutdown temp.	T_{jSD}	150	170	190	°C		
Thermal shutdown hyst.	ΔT	_	10	_	K		
Thermal Resistances							
Junction ambient	$R_{ m thj-a}$	_	185	K/W	_		

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Table 4 Electrical Characteristics

4.5 V < $V_{\rm CC}$ < 5.5 V; 6.0 V < $V_{\rm S}$ < 27 V; $R_{\rm L}$ = 500 Ω ; $V_{\rm ENN}$ < $V_{\rm ENN,ON}$; -40 °C < $T_{\rm j}$ < 125 °C; all voltages with respect to ground; positive current flowing into pin; unless otherwise specified.

Parameter	Symbol	Limit Values			Unit	Remark
		Min.	Тур.	Max.		
Current Consumption	,		1			
Current consumption	$I_{\rm CC}$	_	0.4	0.7	mA	recessive state; $V_{TxD} = V_{CC}$
Current consumption	I_{S}	_	0.5	1.0	mA	recessive state; $V_{TxD} = V_{CC}$
Current consumption	$I_{\rm CC}$	_	0.4	8.0	mA	dominant state; $V_{\text{TxD}} = 0 \text{ V}$; without R_{L}
Current consumption	$I_{\mathbb{S}}$	_	1.3	2.0	mA	dominant state; $V_{\text{TxD}} = 0 \text{ V}$; without R_{L}
Current consumption	$I_{\rm CC}$		0.4	0.7	mA	power-up mode
Current consumption	$I_{\mathbb{S}}$	_	0.5	1.0	mA	power-up mode, $V_{\rm CC} = 0 \ \rm V,$ $V_{\rm S} = 13.5 \ \rm V$
Current consumption	$I_{\rm CC}$	1	3	10	μΑ	stand-by mode
Current consumption	I_{S}	_	18	40	μΑ	stand-by mode

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4.5 V < $V_{\rm CC}$ < 5.5 V; 6.0 V < $V_{\rm S}$ < 27 V; $R_{\rm L}$ = 500 Ω ; $V_{\rm ENN}$ < $V_{\rm ENN,ON}$; -40 °C < $T_{\rm j}$ < 125 °C; all voltages with respect to ground; positive current flowing into pin; unless otherwise specified.

Parameter	Symbol	Lir	Limit Values			Remark
		Min.	Тур.	Max.		
Enable Not Input (pin EN	IN)					
HIGH level input voltage threshold	$V_{ENN,off}$	_	2.8	$V_{\rm CC}$	V	low power mode
LOW level input voltage threshold	$V_{ENN,on}$	$0.3 imes V_{ m CC}$	2.2	_	V	normal operation mode
ENN input hysteresis	$V_{ENN,hys}$	300	600	900	mV	_
ENN pull-up resistance	R_{ENN}	15	30	60	kΩ	_
Receiver Output RxD						
HIGH level output current	$I_{RD,H}$	-1.2	-0.8	-0.5	mA	$V_{RD} = 0.8 \times V_{CC}$
LOW level output current	$I_{RD,L}$	0.5	8.0	1.2	mA	V_{RD} = 0.2 × V_{CC}
Transmission Input TxD	•			*		
HIGH level input voltage threshold	$V_{TD,H}$	_	2.9	$V_{\rm CC}$	V	recessive state
TxD input hysteresis	$V_{TD,hys}$	300	700	900	mV	_
LOW level input voltage threshold	$V_{TD,L}$	$0.3 imes V_{ m CC}$	2.1	-	V	dominant state
TxD pull-up current	I_{TD}	-150	-110	-70	μΑ	$V_{TxD} < 0.3 \times V_{CC}$

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4.5 V < $V_{\rm CC}$ < 5.5 V; 6.0 V < $V_{\rm S}$ < 27 V; $R_{\rm L}$ = 500 Ω ; $V_{\rm ENN}$ < $V_{\rm ENN,ON}$; -40 °C < $T_{\rm j}$ < 125 °C; all voltages with respect to ground; positive current flowing into pin; unless otherwise specified.

Parameter	Symbol	Lir	nit Val	ues	Unit	Remark
		Min.	Тур.	Max.		
Bus Receiver	1					
Receiver threshold voltage, recessive to dominant edge	$V_{ m bus,rd}$	0.44 × V _S	0.48 × V _S	_	V	-8 V < $V_{\rm bus}$ < $V_{\rm bus,dom}$
Receiver threshold voltage, dominant to recessive edge	$V_{ m bus,dr}$	-	0.56 × <i>V</i> _S	$V_{\rm S}$	V	$V_{\rm bus,rec} < V_{\rm bus} < 20 \; \rm V$
Receiver hysteresis	$V_{ m bus,hys}$	0.02 × <i>V</i> _S	0.04 × V _S	$V_{ m S}$	mV	$ V_{\rm bus,hys} = V_{\rm bus,rec} - \\ V_{\rm bus,dom} $
Receiver threshold center voltage	$V_{ m bus,cnt}$	$0.475 \times V_{\rm S}$	$0.5 imes V_{ extsf{S}}$	$0.525 \times V_{\rm S}$		LIN2.0 table 3.1
Input leakage current	$I_{ m bus,lek}$	-1			mA	$\begin{split} V_{\rm bus} &= {\rm OV}, \ V_{\rm bat} = {\rm 12V}, \\ {\rm pull-up \ resistor \ as} \\ {\rm specified \ in \ LIN2.0} \end{split}$
Wake-up threshold voltage	$V_{ m wake}$	0.40 × V _S	$0.5 imes V_{ m S}$	$V_{ m S}$	V	-
Bus Transmitter						
Bus recessive output voltage	$V_{ m bus,rec}$	0.9 × V _S	_	$V_{\mathtt{S}}$	V	$V_{TxD} = V_{CC}$
Bus dominant output voltage	$V_{ m bus,dom}$	0	_	2	V	$V_{TxD} = 0 V$ $7.3V < V_{S} < 27V$
		0	_	1.2	V	$V_{TxD} = 0 \text{ V}$ $6V < V_{S} < 7.3V$
Bus short circuit current	$I_{ m bus,sc}$	40	100	150	mA	$V_{\rm bus,short}$ = 13.5 V
Leakage current	$I_{ m bus,lk}$	-1	-	-	mA	$\begin{split} V_{\mathrm{CC}} &= 0 \text{ V}, \ V_{\mathrm{S}} = 0 \text{ V}, \\ V_{\mathrm{bus}} &= -8 \text{ V}, \end{split}$
		_	10	20	μΑ	$\begin{split} V_{\mathrm{CC}} &= 0 \; \mathrm{V}, \\ V_{\mathrm{S}} &= 13.5 \mathrm{V}, \\ V_{\mathrm{bus}} &= 20 \; \mathrm{V}, \end{split}$
Bus pull-up resistance	R_{bus}	20	30	47	kΩ	_

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4.5 V < $V_{\rm CC}$ < 5.5 V; 6.0 V < $V_{\rm S}$ < 27 V; $R_{\rm L}$ = 500 Ω ; $V_{\rm ENN}$ < $V_{\rm ENN,ON}$; -40 °C < $T_{\rm j}$ < 125 °C; all voltages with respect to ground; positive current flowing into pin; unless otherwise specified.

Parameter	Symbol	Liı	mit Val	ues	Unit	Remark
		Min.	Тур.	Max.		
Dynamic Transceiver Ch	aracteris	tics				
Falling edge slew rate	$S_{bus(L)}$	-3	-2.0	-1	V/µs	$ \begin{array}{c} ^{1)} 60\% > V_{\rm bus} > 40\% \\ 1 \ \mu {\rm s} < (\tau = R_{\rm L} \times C_{\rm BUS}) < 5 \ \mu {\rm s}; \\ V_{\rm CC} = 5 \ {\rm V}; \\ V_{\rm S} = 13.5 \ {\rm V} \end{array} $
Rising edge slew rate	$S_{bus(H)}$	1	1.5	3	V/µs	$ \begin{array}{c} ^{1)} \ 40\% < V_{\rm bus} < 60\% \\ 1 \ \mu {\rm s} < (\tau = R_{\rm L} \times C_{\rm BUS}) < 5 \ \mu {\rm s}; \\ V_{\rm CC} = 5 \ {\rm V}; \\ V_{\rm S} = 13.5 \ {\rm V} \end{array} $
Slope symmetry	t _{slopesym}	5		-5	μs	t_{fslope} - t_{rslope} V_{S} = 18 V
Propagation delay TxD LOW to bus	$t_{d(L),T}$	-	1	3	μs	$V_{\rm CC}$ = 5 V
Propagation delay TxD HIGH to bus	$t_{d(H),T}$	-	1	3	μs	$V_{\rm CC}$ = 5 V
Propagation delay bus dominant to RxD LOW	$t_{\sf d(L),R}$	_	1	6	μs	$V_{\rm CC}$ = 5 V; $C_{\rm RxD}$ = 20 pF
Propagation delay bus recessive to RxD HIGH	$t_{\sf d(H),R}$	_	1	6	μs	$V_{\rm CC}$ = 5 V; $C_{\rm RxD}$ = 20 pF
Receiver delay symmetry	$t_{\rm sym,R}$	-2	_	2	μs	$t_{\text{sym,R}} = t_{\text{d(L),R}} - t_{\text{d(H),R}}$
Transmitter delay symmetry	$t_{sym,T}$	-2	_	2	μs	$t_{\text{sym,T}} = t_{\text{d(L),T}} - t_{\text{d(H),T}}$
Duty cycle D1	t _{duty1}	0.396	_	-	μs	$\begin{array}{l} \text{duty cycle 1}^{1)} \\ \text{TH}_{\text{Rec}}(\text{max}) = 0.744 \times V_{\text{S}}; \\ \text{TH}_{\text{Dom}}(\text{max}) = 0.581 \times V_{\text{S}}; \\ V_{\text{S}} = 7.0 \dots 18 \text{V}; \\ t_{\text{bit}} = 50 \mu\text{s}; \\ \text{D1} = t_{\text{bus_rec}(\text{min})} / 2 t_{\text{bit}}; \end{array}$
Duty cycle D2	t _{duty2}		_	0.581	μs	

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Parameter	Symbol	Limit Values			Unit	Remark
		Min.	Тур.	Max.		
Wake-up delay time	t _{wake}	30	100	150	μs	<i>T</i> _j < 125 °C
				170	μs	<i>T</i> _j < 150 °C
Delay time for mode change	t _{snorm}			50	μs	

¹⁾ Bus load conditions concerning LIN spec 2.0 $C_{\rm bus}$, $R_{\rm bus}$ = 1 nF, 1 k Ω / 6.8 nF, 660 Ω / 10 nF, 500 Ω

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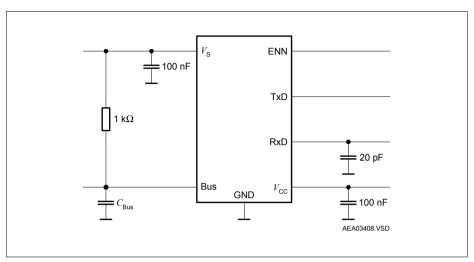


Figure 4 Test Circuits

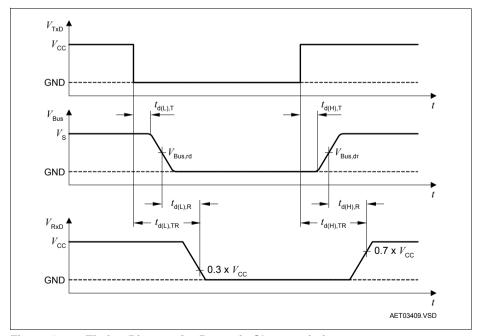


Figure 5 Timing Diagram for Dynamic Characteristics

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Application

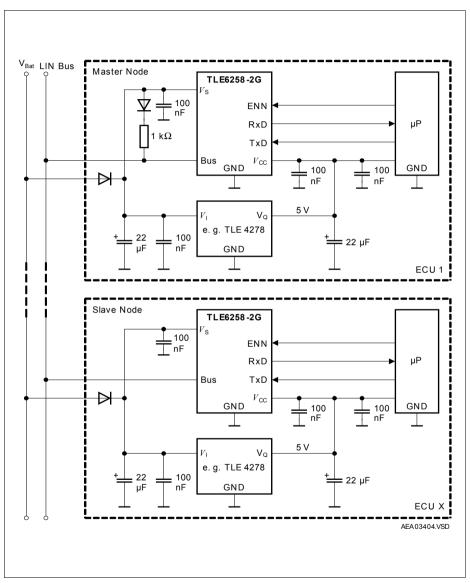


Figure 6 Application Circuit

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Package Outlines

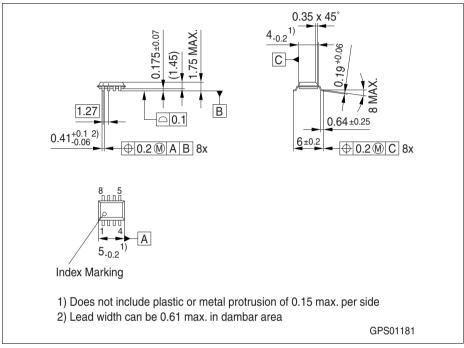


Figure 7 PG-DSO-8 (PG-DSO-8-16 Plastic Dual Small Outline)

Green Product (RoHS compliant)

To meet the world-wide customer requirements for environmentally friendly products and to be compliant with government regulations the device is available as a green product. Green products are RoHS-Compliant (i.e Pb-free finish on leads and suitable for Pb-free soldering according to IPC/JEDEC J-STD-020).

You can find all of our packages, sorts of packing and others in our Infineon Internet Page "Products": http://www.infineon.com/products.

Dimensions in mm



Revision History

Version	Date	Changes						
Rev. 2.1	2007-08-08	 All pages: Infineon logo updated Page 3: added "AEC qualified" and "RoHS" logo, "Green Product (RoHS compliant)" and "AEC qualified" statement added to feature list, package name changed to RoHS compliant versions, package picture updated, ordering code removed Page 15: Changed package drawing to GPS01181 Package name changed to RoHS compliant versions, "Green Product" description added added Revision History 						
		versions, package picture updated, ordering code removed • Page 15: Changed package drawing to GPS01181 Package name changed to RoHS compliant versions "Green Product" description added						

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